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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO. CONFIRMATION NO.		
09/894,334	06/27/2001	Qing Ma	42390P10606	6477	
8791	7590 02/22/2005	EXAMINER			
	SOKOLOFF TAYLO	COLEMAN, WILLIAM D			
12400 WILS SEVENTH F	HIRE BOULEVARD LOOR	ART UNIT	PAPER NUMBER		
LOS ANGEI	LES, CA 90025-1030	2823			
		DATE MAILED: 02/22/2005			

Please find below and/or attached an Office communication concerning this application or proceeding.

Attachment(s)

Notice of References Cited (PTO-892)

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2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date \_\_\_\_\_.

4) 🔲	Interview Summary (PTO-413
	Paner No(s)/Mail Date

5) Notice of Informal Patent Application (PTO-152)

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#### **DETAILED ACTION**

## Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on December 20, 2004 has been entered.

### Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.
- 3. The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).
- 4. Claims 1,3-5,7, 8 and 10-12 are rejected under 35 U.S.C. 102(e) as being anticipated by Hung et al., U.S. Patent 6,329,738 B1.

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5. <u>Hung</u> discloses a semiconductor process as claimed. Please see **FIGS. 1-24**, where <u>Hung</u> teaches the following limitations.

FIG.23J

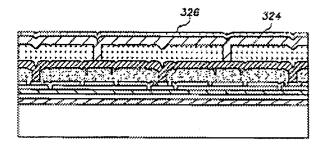
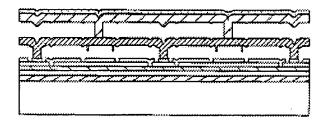


FIG.23K



6. Pertaining to claim 1, <u>Hung</u> teaches a method comprising:

Over an area of a substrate, forming a plurality of three dimensional first structures each including lateral side portions defining a distance from the surface of the substrate; following forming the plurality of first structures, conformally introducing a sacrificial material 320 over the area of the substrate including on the lateral side portions of the plurality of first structures;

introducing a second structural material 324/326 over the sacrificial material;

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exposing a portion of the sacrificial and a superior surface of the plurality of first structures, the superior surface opposing the surface of the substrate; and removing the sacrificial material;

wherein removing the sacrificial material comprises suspending the second structural material as a second structure electrically coupled to the first structure

- 7. Pertaining to claim 3, <u>Hung</u> teaches the method of claim 1, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
- 8. Pertaining to claim 4, <u>Hung</u> teaches the method of claim 1, prior to introducing the second structural material, further comprising patterning the sacrificial material (please note that sacrificial material 312 is patterned).
- 9. Pertaining to claim 5, <u>Hung</u> teaches the method of claim 1, wherein the first structural material comprises silicon and the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.
- 10. Pertaining to claim 8, <u>Hung</u> teaches a method comprising:

  over an area of a surface of a substrate, lithographically patterning a plurality of first structures
  each including lateral side portions defining a distance from the surface of the substrate, the
  plurality of first structures having a first dimension about the surface of the substrate and a
  second different dimension;

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following forming the plurality of first structures, conformally introducing a sacrificial material layer over the area of the substrate including on the lateral side portions of the plurality of first structures;

patterning the sacrificial material to expose a superior surface of the plurality of first structures, the superior surface opposing the surface of the substrate;

forming second structures over the sacrificial material; and removing the sacrificial material;

wherein removing the sacrificial material comprises suspending the second structure by the first structure, and wherein the second structure is electrically coupled to the first structure.

11. Pertaining to claim 10, Hung teaches the method of claim 8, wherein the sacrificial material comprises silicon dioxide and introducing the sacrificial material and comprises growing.

### **Objections**

- 12. The Examiner objects to the term "superior" because there is no support in the specification for such a term, furthermore the term would not be enforced by the courts if the Application became a patent.
- 13. Claims 7, 10 and 11 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

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#### Conclusion

- 14. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 571-272-1856. The examiner can normally be reached on Monday-Friday 9:00 AM-5:30 PM.
- 15. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.
- 16. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

W. David Coleman Primary Examiner Art Unit 2823